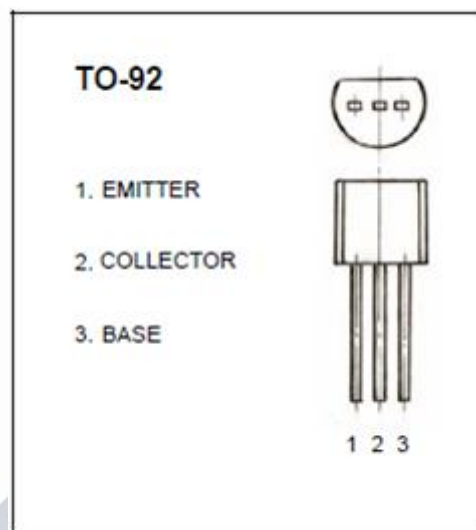


isc Silicon NPN Transistor**2SC2120****DESCRIPTION**

- High $h_{FE}(1)=100-320$
- 1 Watts Amplifier Applications
- Complement to Type 2SA950

APPLICATIONS

- Audio power amplifier Applications

**ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	35	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	800	mA
I_B	Base Current	160	mA
P_C	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	600	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$

isc Silicon NPN Transistor**2SC2120****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA; I _B = 0	30			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 500mA ; I _B = 20mA			0.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 10mA ; V _{CE} = 1V	0.5		0.8	V
I _{CBO}	Emitter Cutoff Current	V _{CB} = 35V; I _E = 0			0.1	μ A
I _{EBO}	Collector Cutoff Current	V _{EB} = 5V; I _C = 0			0.1	μ A
h _{FE(1)}	DC Current Gain	I _C = 0.1A ; V _{CE} = 1V	100		320	
h _{FE(2)}	DC Current Gain	I _C = 0.7A ; V _{CE} = 1V	35			
f _T	Current-Gain—Bandwidth Product	I _C = 10mA; V _{CE} = 5V; f= 100MHz		120		MHz
C _{ob}	Collector Output Capacitance	V _{CB} =10V; I _E =0; f=1MHz		13		pF

◆ **h_{FE(1)} Classifications**

O	Y
100-200	160-320